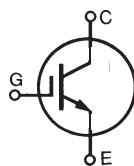


GenX3™ 600V IGBT

IXGL200N60B3

Medium speed low V_{sat} PT
IGBTs 5-40 kHz switching

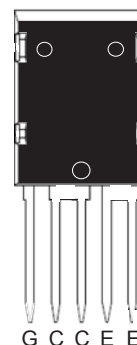


$$V_{CES} = 600V$$

$$I_{C110} = 90A$$

$$V_{CE(sat)} \leq 1.50V$$

$$t_{fi(typ)} = 183ns$$



G = Gate C = Collector
E = Emitter

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $150^\circ C$	600	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$ (limited by leads)	150	A
I_{C110}	$T_C = 110^\circ C$ (chip capability)	90	A
I_{CM}	$T_C = 25^\circ C$, 1ms	600	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 125^\circ C$, $R_G = 1\Omega$ Clamped inductive load @ $V_{CE} \leq 600V$	$I_{CM} = 300$	A
P_C	$T_C = 25^\circ C$	400	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	Maximum lead temperature for soldering	300	$^\circ C$
T_{SOLD}	Plastic body for 10s	260	$^\circ C$
V_{ISOL}	50/60Hz, RMS, 1 minute	2500	V~
	$I_{ISOL} \leq 1mA$ $t = 1s$	3000	V~
F_C	Mounting force	20..120/4.5..27	N/lb.
Weight		8	g

Symbol	Test Conditions ($T_J = 25^\circ C$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	600		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	3.0		V
I_{CES}	$V_{CE} = V_{CES}$ $V_{GE} = 0V$ $T_J = 125^\circ C$			200 μA 2 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 100A$, $V_{GE} = 15V$, Note 1 $I_C = 200A$ $T_J = 125^\circ C$	1.35 1.65 1.75	1.50	V V V

Features

- Silocon chip on Direct-Copper Bond (DCB) substrate
- Isolated mounting surface
- Square RBSOA
- High current handling capability
- 2500V electrical isolation

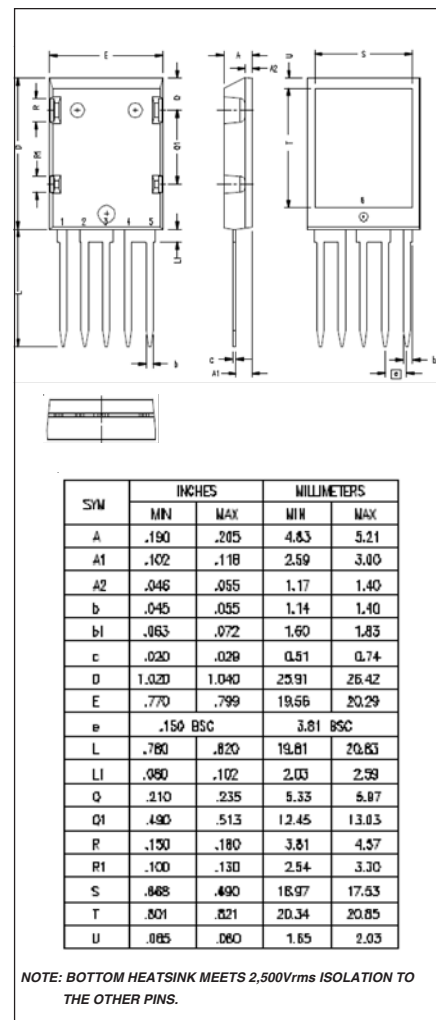
Advantages

- High power density
- Low gate drive requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 60\text{A}$, $V_{CE} = 10\text{V}$, Note 1	95	160	S
C_{ies}	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$		26	nF
C_{oes}			1260	pF
C_{res}			97	pF
Q_g	$I_C = 100\text{A}$, $V_{GE} = 15\text{V}$, $V_{CE} = 0.5 \cdot V_{CES}$		750	nC
Q_{ge}			115	nC
Q_{gc}			245	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 100\text{A}$, $V_{GE} = 15\text{V}$ $V_{CE} = 300\text{V}$, $R_G = 1\Omega$		44	ns
t_{ri}			83	ns
E_{on}			1.6	mJ
$t_{d(off)}$			310	ns
t_{fi}			183	ns
E_{off}			2.9	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 100\text{A}$, $V_{GE} = 15\text{V}$ $V_{CE} = 300\text{V}$, $R_G = 1\Omega$		42	ns
t_{ri}			80	ns
E_{on}			2.4	mJ
$t_{d(off)}$			430	ns
t_{fi}			300	ns
E_{off}			4.2	mJ
R_{thJC}			0.11	0.31°C/W
R_{thCS}				$^\circ\text{C/W}$

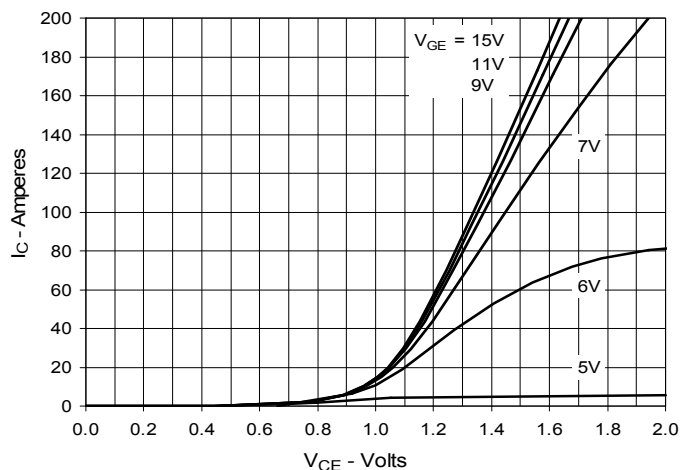


Note 1: Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.

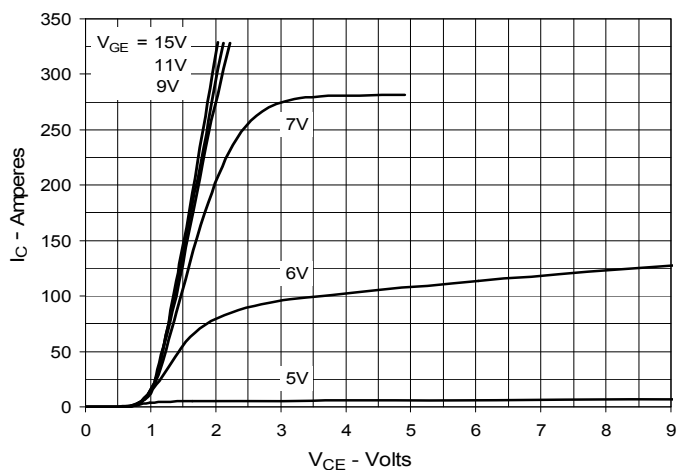
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

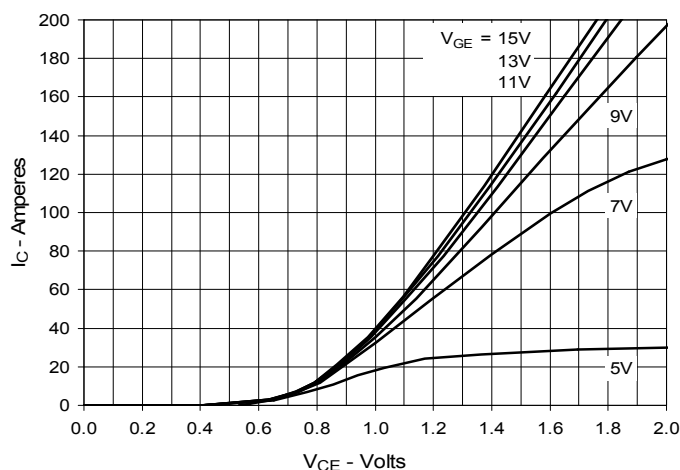
**Fig. 1. Output Characteristics
@ 25°C**



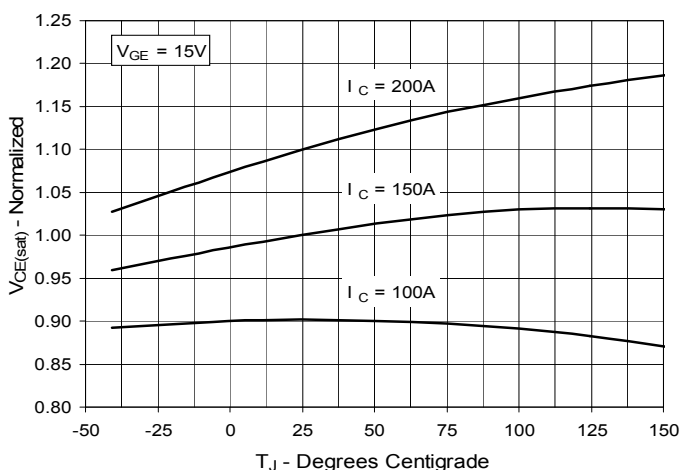
**Fig. 2. Extended Output Characteristics
@ 25°C**



**Fig. 3. Output Characteristics
@ 125°C**



**Fig. 4. Dependence of $V_{CE(sat)}$ on
Junction Temperature**



**Fig. 5. Collector-to-Emitter Voltage
vs. Gate-to-Emitter Voltage**

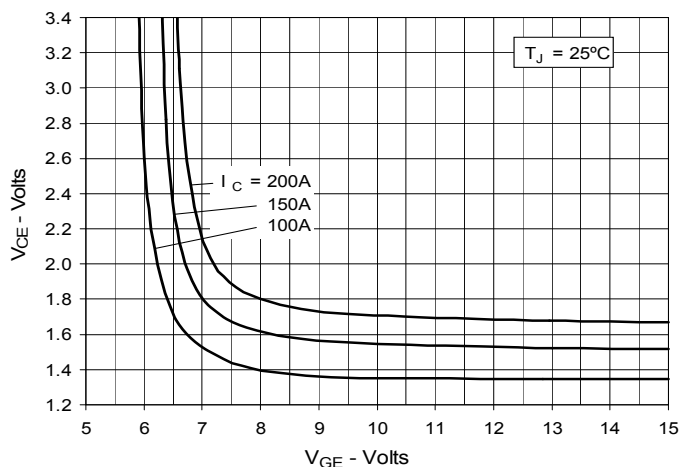


Fig. 6. Input Admittance

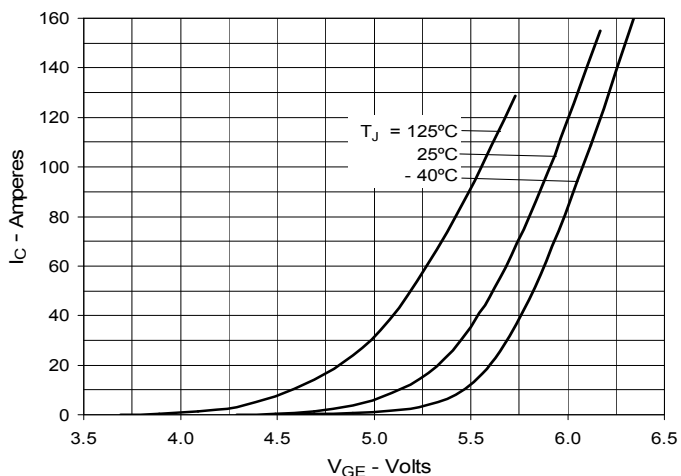
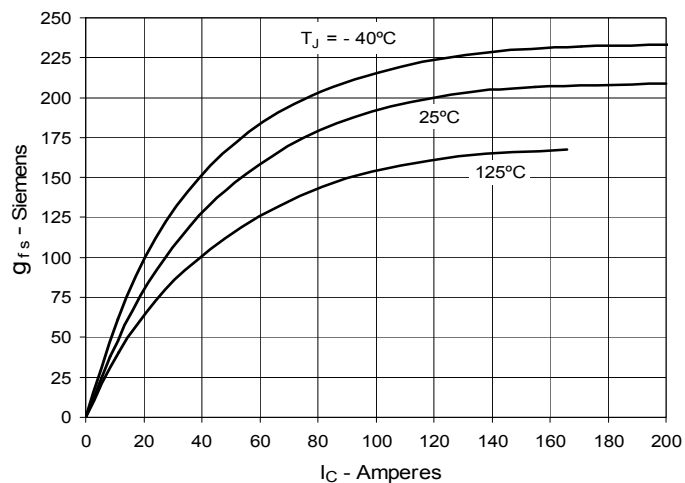
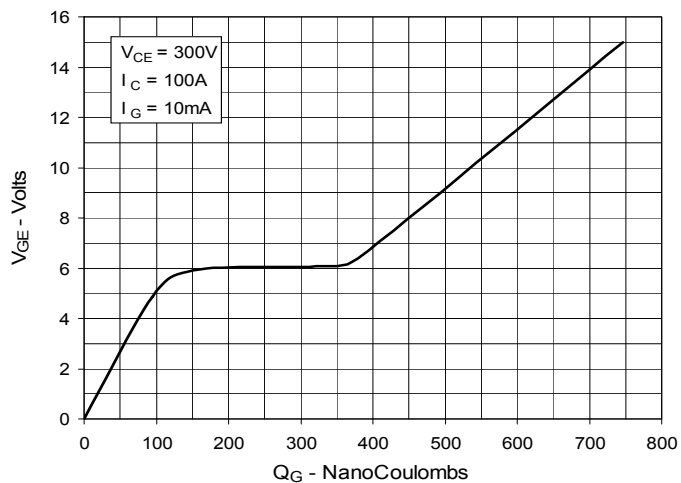
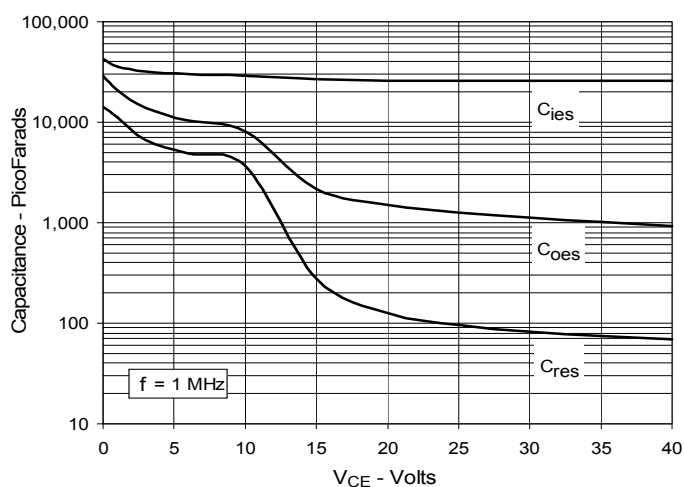
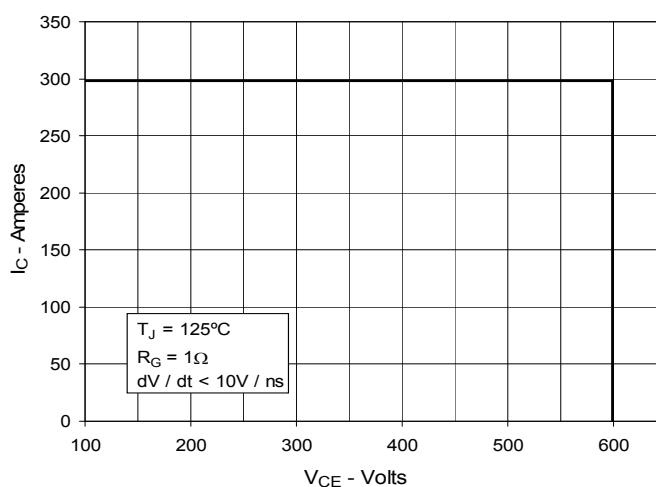
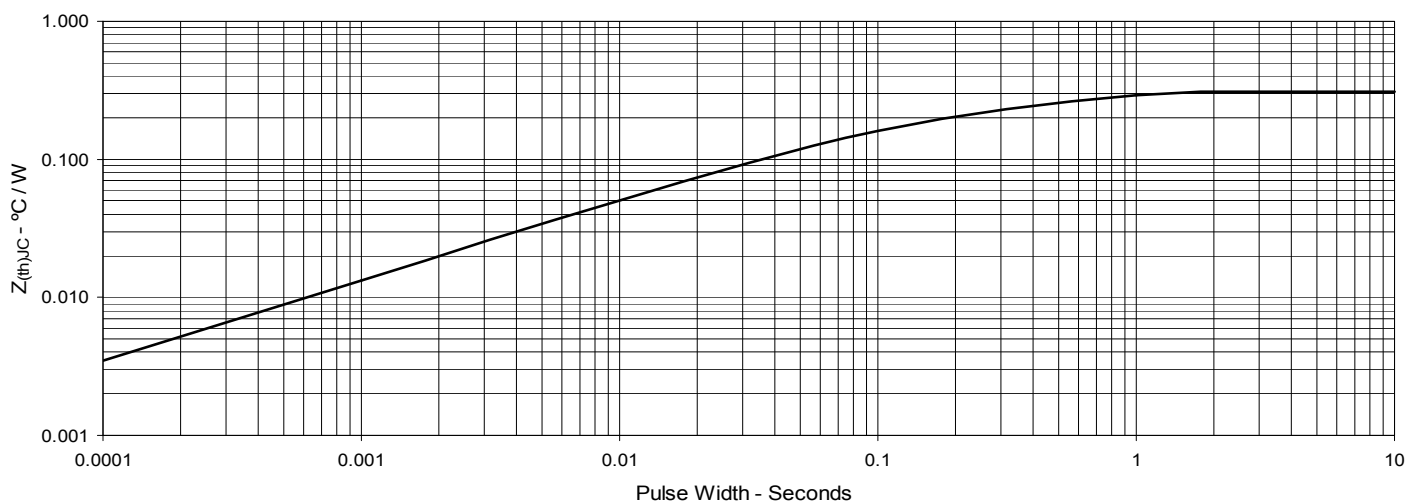
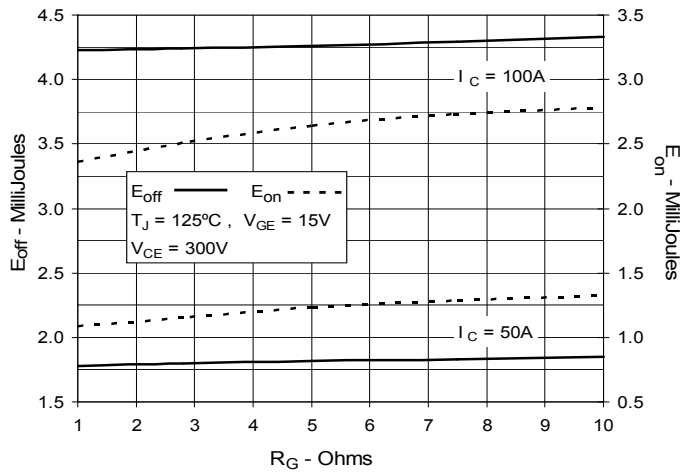


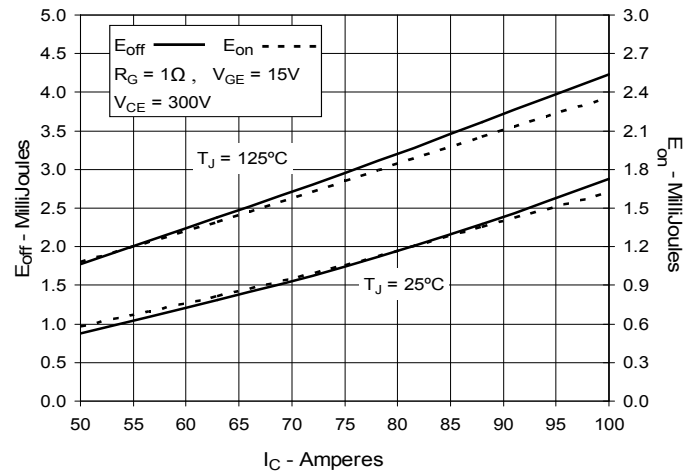
Fig. 7. Transconductance

Fig. 8. Gate Charge

Fig. 9. Capacitance

Fig. 10. Reverse-Bias Safe Operating Area

Fig. 11. Maximum Transient Thermal Impedance


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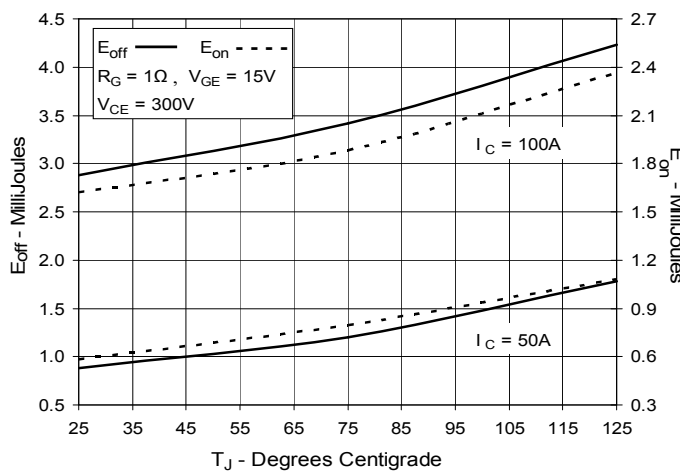
**Fig. 12. Inductive Switching
Energy Loss vs. Gate Resistance**



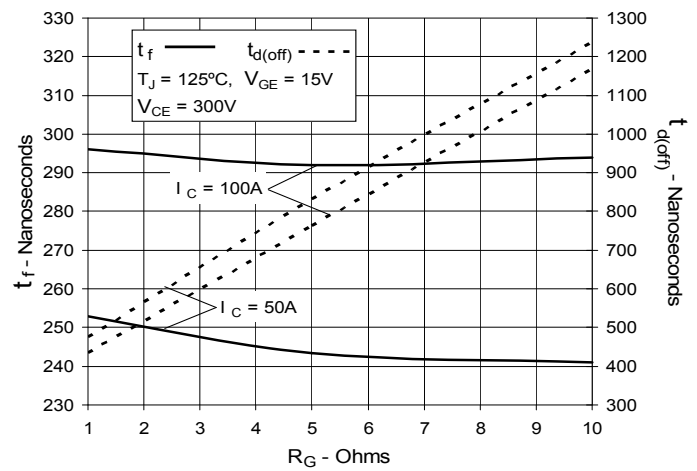
**Fig. 13. Inductive Switching
Energy Loss vs. Collector Current**



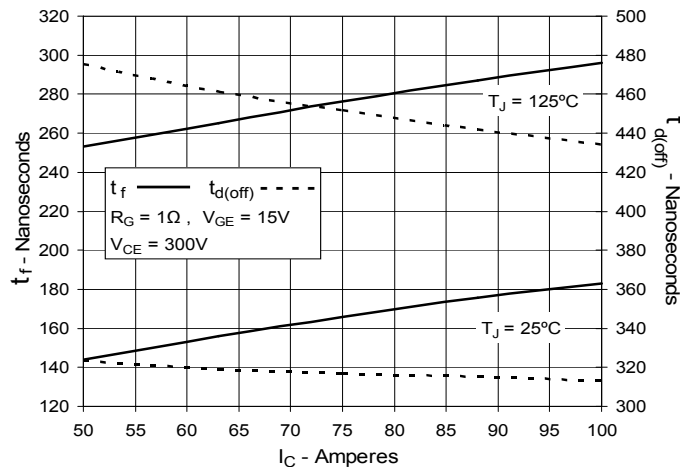
**Fig. 14. Inductive Switching
Energy Loss vs. Junction Temperature**



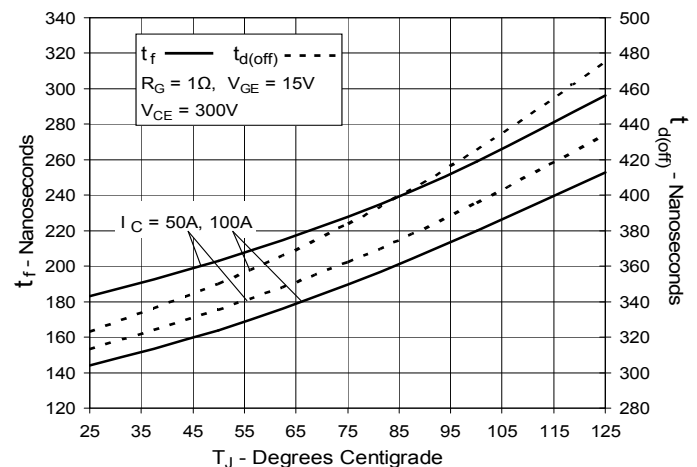
**Fig. 15. Inductive Turn-off
Switching Times vs. Gate Resistance**



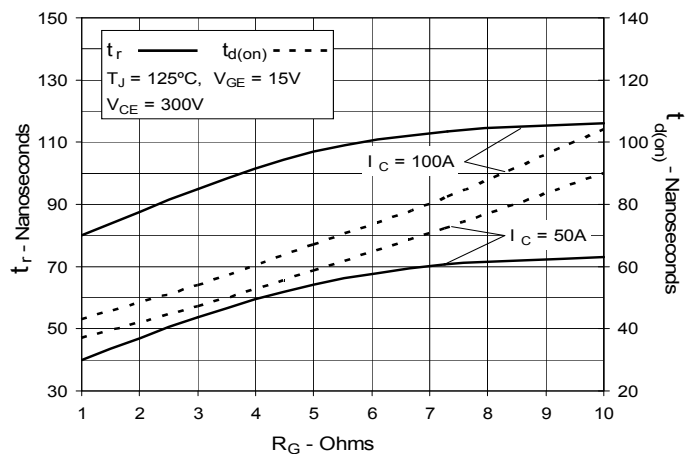
**Fig. 16. Inductive Turn-off
Switching Times vs. Collector Current**



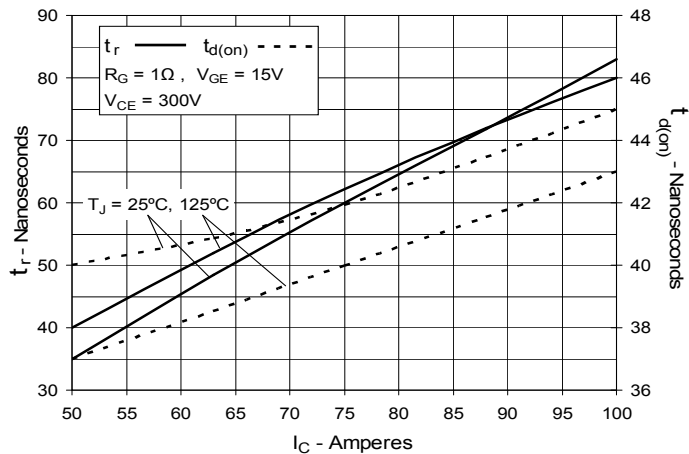
**Fig. 17. Inductive Turn-off
Switching Times vs. Junction Temperature**



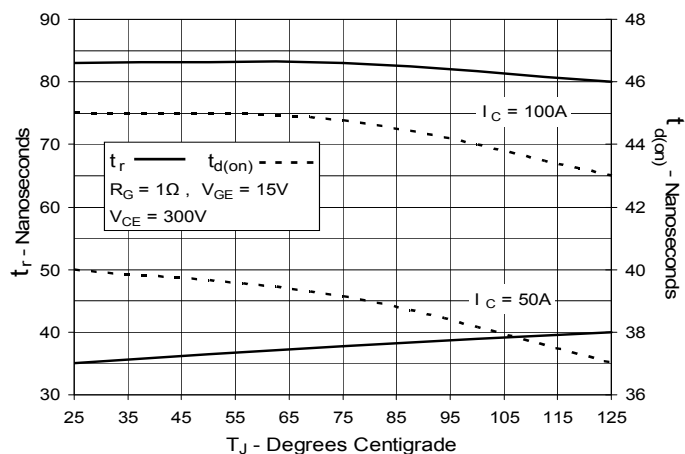
**Fig. 18. Inductive Turn-on
Switching Times vs. Gate Resistance**



**Fig. 19. Inductive Turn-on
Switching Times vs. Collector Current**



**Fig. 20. Inductive Turn-on
Switching Times vs. Junction Temperature**





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